

Photosensor with front-end IC

S13282-01CR

Compact APD suitable for various light level detection

The S13282-01CR is a compact optical device that integrates a Si APD and preamp. It has a built-in DC feedback circuit for reducing the effects of background light. It also provides excellent noise and frequency characteristics. We provide an evaluation kit for this product. Contact us for detailed information.

Features

- High-speed response: 180 MHz
- Two-level gain switch function (low gain: single output, high gain: defferential output)
- Reduced background light effects
- Small waveform distortion when excessive light is incident

Applications

- Distance measurement
- Option
- Driver circuit

C13283-03

Structure

Parameter	Symbol	Specification	Unit
Detector	-	Si APD	-
Photosensitive area size*1	A	ф0.2	mm
Package	-	Plastic	-

*1: Photosensitive area in which a typical gain can be obtained

Absolute maximum ratings

Parameter	Symbol	Condition	Value	Unit
Supply voltage (for preamp)	Vcc max		4.5	V
Reverse voltage (for APD)	V_APD		0 to V _{BR}	V
Reverse current (DC)	IR max		0.2	mA
Forward current	IF max		10	mA
DCFB terminal voltage	-		Vcc + 0.7	V
Gain terminal voltage	-		Vcc + 0.7	V
Operating temperature	Topr	No dew condensation*2	-30 to +85	°C
Storage temperature	Tstg	No dew condensation*2	-30 to +85	°C
Soldering conditions*3	-		Peak temperature 240 °C, 1 time (see P.5)	-

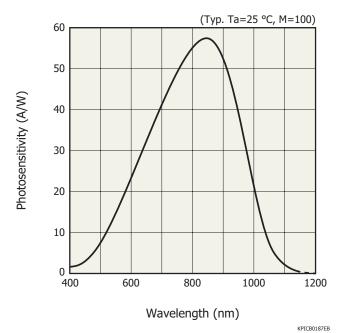
 *2: When there is a temperature difference between a product and the surrounding area in high humidity environment, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.
*3: JEDEC level 5a

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

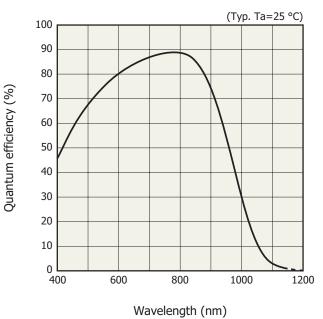
Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Spectral response range	λ		400 to 1150		nm	
Peak sensitivity wavelength	λр	M=100	-	840	-	nm
Photosensitivity	S	λ=λp, M=100, low gain	0.1	0.2	0.4	- MV/W
		λ=λp, M=100, high gain	2	4	8	
Quantum efficiency	QE	λ=900 nm, M=1	-	70	-	%
Breakdown voltage	VBR	ID=100 μA	120	160	200	V
Temperature coefficient of breakdown voltage	ΔTVbr		-	1.1	-	V/°C
Dark current	ID	M=100	10	100	1000	pА
Temperature coefficient of dark current	ΔTid	M=100	-	1.1	-	times/°C
Current consumption	Ic	Low gain	17	25	32	mA
Current consumption		High gain	20	28	35	
Low cutoff frequency	fcl	Low gain	-	0.01	-	MHz
		High gain	-	0.5	-	
High cutoff frequency	fch	Low gain	120	180	240	MHz
		High gain	100	160	220	
Input conversion noise power	en	f=10 MHz, M=100	-	50	100	fW/Hz ^{1/2}
		f=100 MHz, M=100	-	65	130	
Output voltage level	-	Low gain	0.6	0.9	1.2	V
		High gain	0.7	1	1.3	
Output offset voltage	Voffset	High gain	-	-	±100	mV
Maximum output voltage	Vp-p max	Low gain	-	-0.5	-	- V
amplitude		High gain	-	±0.7	-	
Supply voltage	Vcc1, Vcc2		3.135	3.3	3.465	V

Electrical and optical characteristics (Ta=25 °C)

Spectral response

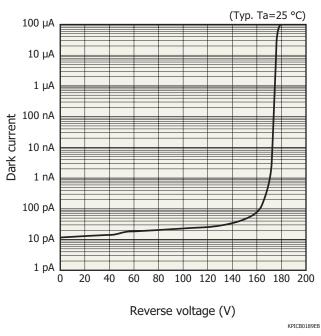


Quantum efficiency vs. wavelength



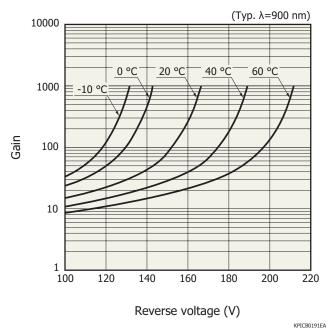
KPICB0188EA



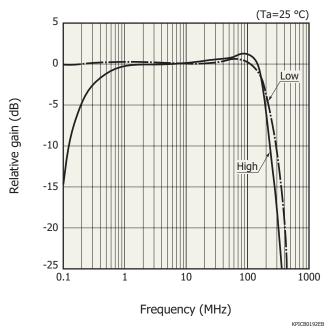


Dark current vs. reverse voltage



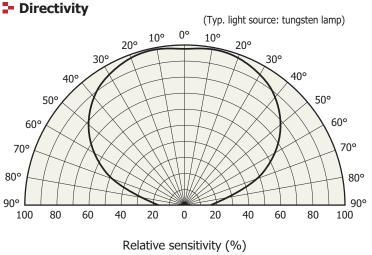


Frequency characteristics (typical example)





Photosensor with front-end IC



KPICB0193EA

Truth table

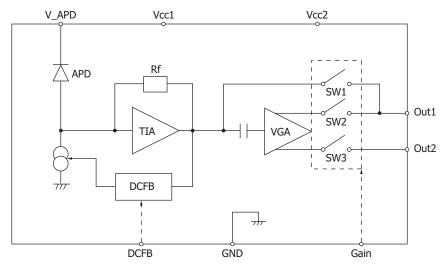
Gain selection

Gain selection	Gain		
0	Low gain (× 1)		
1	High gain (× 20)		

DCFB_dis selection

DCFB_dis selection	Background light elimination function		
0	ON		
1	OFF		

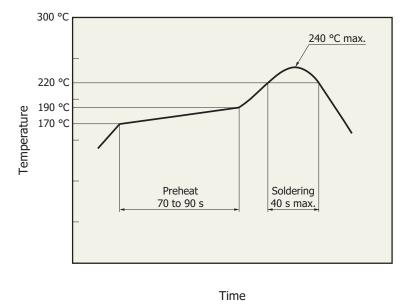
Block diagram



The DCFB (DC feedback) circuit detects the DC component of photocurrent, and reduces the effects of background light through the differential processor.

KPICC0285ED



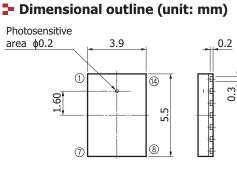


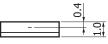
Measured example of temperature profile with our hot-air reflow oven for product testing

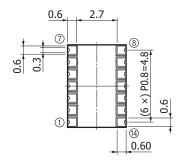
KPICB0171EA

• This product supports lead-free soldering. After unpacking, store it in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform soldering within 24 hours.

• The effect that the product receives during reflow soldering varies depending on the circuit board and reflow oven that are used. Before actual reflow soldering, check for any problems by testing out the reflow soldering methods in advance.





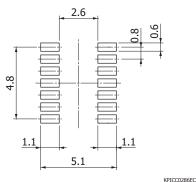


Tolerance unless otherwise noted: ±0.1

Pin no.	Function	Pin no.	Function
1	NC	8	Out2
2	NC	9	GND
3	GND	10	Gain
4	GND	1	Vcc2
5	DCFB	12	Vcc1
6	GND	13	NC
7	Out1	14	V_APD

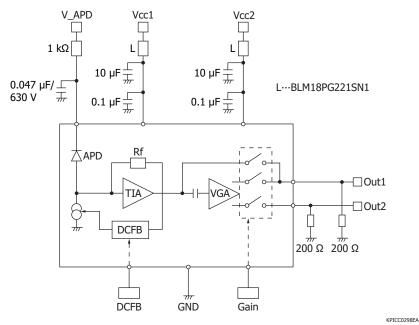
KPICA0100EE

Recommended land pattern (unit: mm)



HAMAMATSU

Connection example



Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
- Disclaimer
- · Metal, ceramic, plastic packages
- · Surface mount type products

Evaluation kit for photosensor with front-end IC (S13282-01CR)

An evaluation kit [48 mm (H) \times 50 mm (V)] for understanding the operating principle of Hamamatsu's S13282-01CR photosensor with front-end IC is available. Contact us for detailed information.





Information described in this material is current as of November 2018.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use. Copying or reprinting the contents described in this material in whole or in part is prohibited without our prior permission.



HAMAMATSU PHOTONICS K.K., Solid State Division

HAMAMA ISU PHOTOVILS K.K., Solid State Division 1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184 U.S.A: Hamamatsu Corporation: 360 Foothill Road, Bridgewater, N.J. 08807, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218, E-mail: usa@hamamatsu.com Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 8152-375-0, Fax: (49) 8152-265-8, E-mail: info@hamamatsu.de France: Hamamatsu Photonics France S.A.R.L: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: (31) 05 37 11 00, Fax: 33-(1) 69 53 71 10, Fax: 33-(1) 69 53 71 10, Fax: (47) 1707-23787, E-mail: info@hamamatsu.fr United Kingdom: Hamamatsu Photonics Norden AB: Torshamnsgatan 35 16440 Kista, Sweden, Telephone: (47) 18W, United Kingdom, Telephone: (47) 707-29878, Fax: (44) 1707-23777, E-mail: info@hamamatsu.ee Italy: Hamamatsu Photonics Italia S.r.I: Strada della Moia, I int. 6, 20020 Arese (Milano), Italy, Telephone: (39)02-93 58 17 33, Fax: (39)02-93 58 17 41, E-mail: info@hamamatsu.it China: Hamamatsu Photonics (China) Co., Itd.: B1201, Jiaming Center, No.27 Dongsanhauna Bellu, Chaoyang District, Beling 100020, China, Telephone: (86) 10-6586-6006, Fax: (86) 10-6586-6006,

www.hamamatsu.com